

MOS FIELD EFFECT TRANSISTOR 2SK3638

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3638 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3638-ZK	TO-252 (MP-3ZK)

FEATURES

· Low on-state resistance

 $R_{DS(on)1}$ = 8.5 m Ω MAX. (Vgs = 10 V, ID = 32 A)

 $R_{DS(on)2} = 15 \text{ m}\Omega \text{ MAX.} \text{ (V}_{GS} = 4.5 \text{ V}, I_{D} = 18 \text{ A})$

- Low Ciss: Ciss = 1100 pF TYP.
- Built-in gate protection diode

(TO-252)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (VGS = 0 V)	VDSS	20	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	٧
Drain Current (DC) (Tc = 25°C)	ID(DC)	±64	Α
Drain Current (pulse) Note	ID(pulse)	±220	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	36	W
Total Power Dissipation	P _{T2}	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Note PW \leq 10 μ s, Duty Cycle \leq 1%

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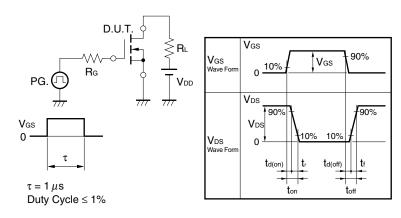


ELECTRICAL CHARACTERISTICS (TA = 25°C)

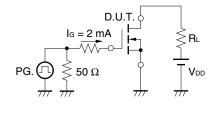
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	loss	V _{DS} = 20 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5		2.5	V
Forward Transfer Admittance Note	yfs	V _{DS} = 10 V, I _D = 32 A	12	25		S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 32 A		6.8	8.5	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 18 A		10	15	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		1100		pF
Output Capacitance	Coss	V _{GS} = 0 V		450		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		170		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10 V, I _D = 32 A		10		ns
Rise Time	tr	V _{GS} = 10 V		4.3		ns
Turn-off Delay Time	t d(off)	R _G = 10 Ω		35		ns
Fall Time	tr			9.7		ns
Total Gate Charge	Q _G	V _{DD} = 16 V		22		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		4.3		nC
Gate to Drain Charge	Q _{GD}	I _D = 64 A		5.1		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 64 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	trr	I _F = 64 A, V _{GS} = 0 V		31		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		23		nC

Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 SWITCHING TIME

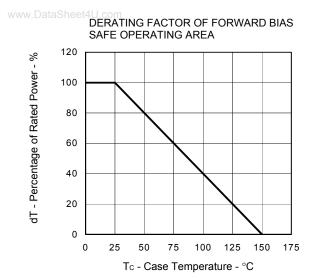


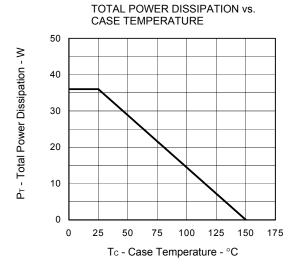
TEST CIRCUIT 2 GATE CHARGE



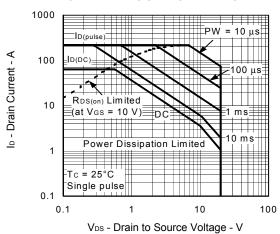


TYPICAL CHARACTERISTICS (TA = 25°C)

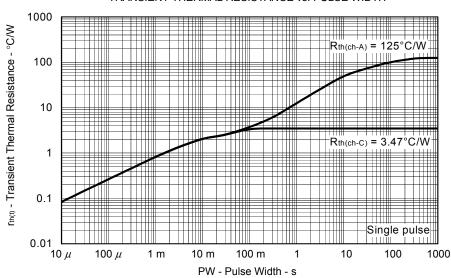




FORWARD BIAS SAFE OPERATING AREA

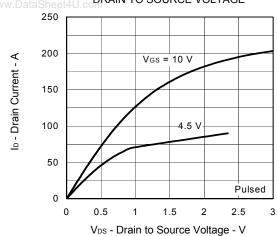


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

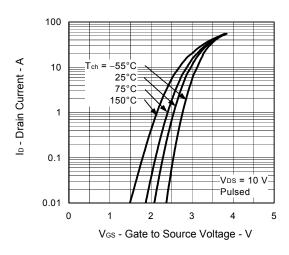




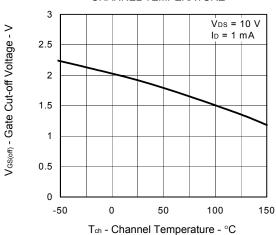
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



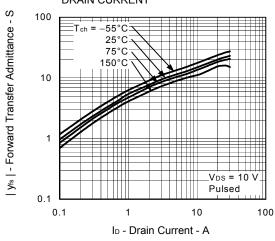
FORWARD TRANSFER CHARACTERISTICS



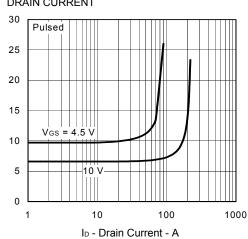
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



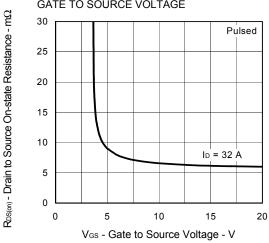
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



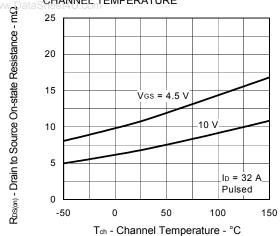
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



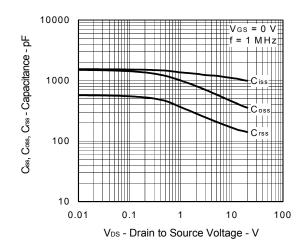
R_{DS(m)} - Drain to Source On-state Resistance - mΩ



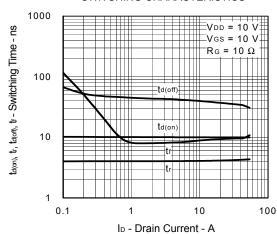
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



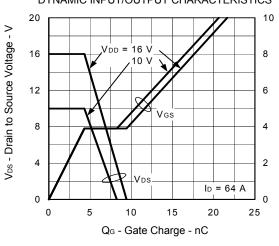
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



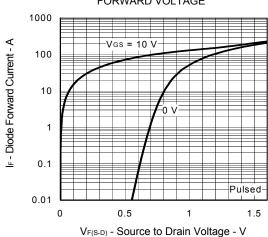
SWITCHING CHARACTERISTICS



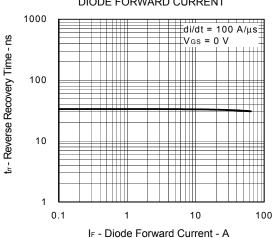
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

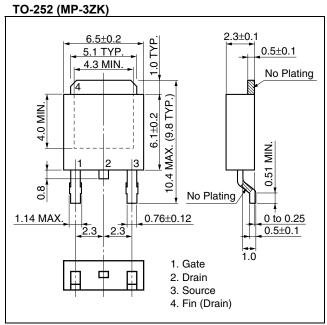


Ves - Gate to Source Voltage - V

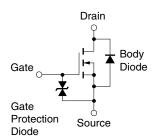


★ PACKAGE DRAWING (Unit: mm)

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EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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